

FIG. 1A

PRIOR ART

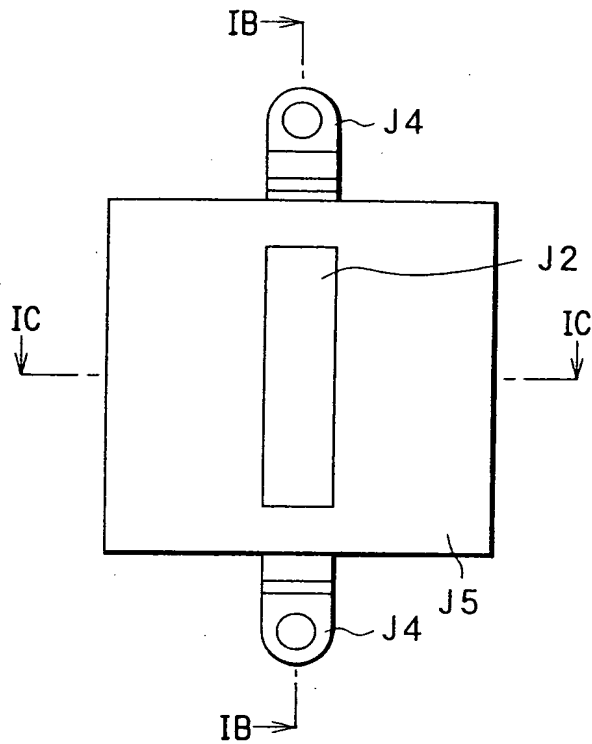


FIG. 1B

PRIOR ART

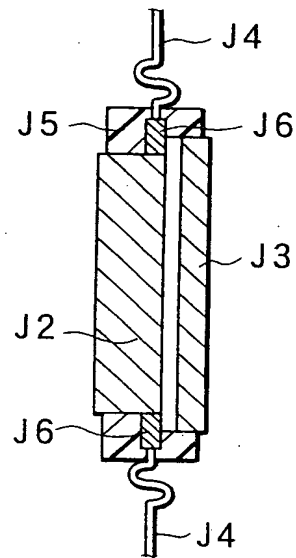
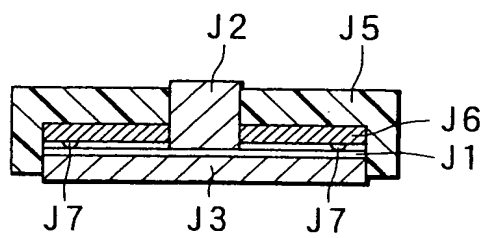


FIG. 1C

PRIOR ART



[illegible]

FIG. 3

NAME OF METAL	CHEMICAL COMPOSITION (%)													
	Fe	Zn	P	Ni	Si	Sn	NiB	Mn	Mg	Cr	Ti	B	Cu	Al
METAL a	2.3	0.1	0.03										REMAIN.	
METAL b	2.4	0.12	0.03										REMAIN.	
METAL c				3.0	0.7								REMAIN.	
METAL d	1.5	0.5				0.5							REMAIN.	
METAL e	1.0	0.05	0.1			1.0							REMAIN.	
METAL f	0.75		0.03			1.25							REMAIN.	
METAL g	0.05 0.15		0.025 0.040										REMAIN.	
METAL h	0.05 0.4		0.05 0.1			0.05 0.2	0.05 0.45						REMAIN.	
METAL i			0.15 OR LOWER	0.1 0.4		1.7 2.3							REMAIN.	
METAL j		0.2 0.35		3.0 3.4	0.6 0.75	1.0 1.5							REMAIN.	
METAL k	0.12 1.0	0.03 0.1			0.1 1.0			0.02 0.05	0.02 0.05		0.02 0.05		0.03 0.2	REMAIN.
METAL l	0.5	0.1			0.3 0.7			0.05	0.35 0.5	0.03		0.06	0.1	REMAIN.

FIG. 4A

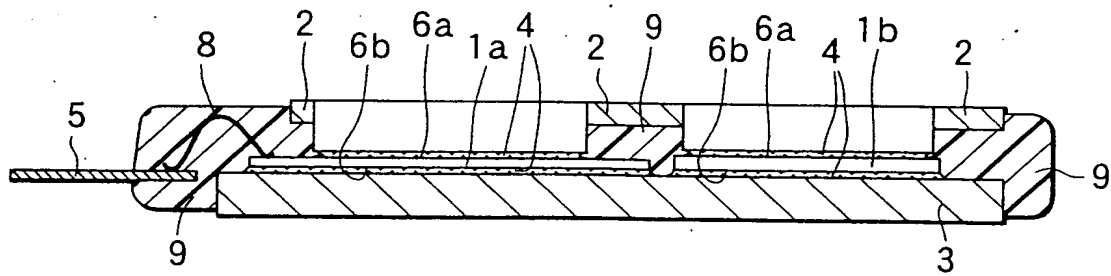


FIG. 4B

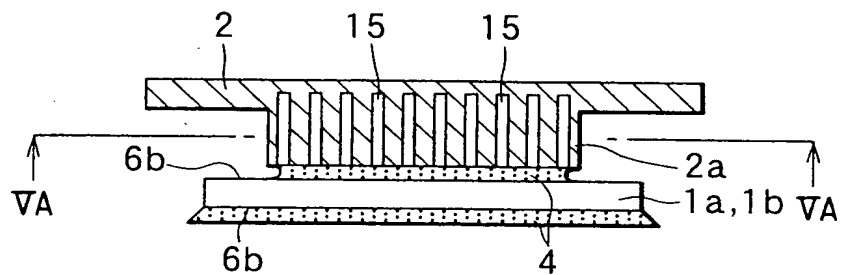


FIG. 4C

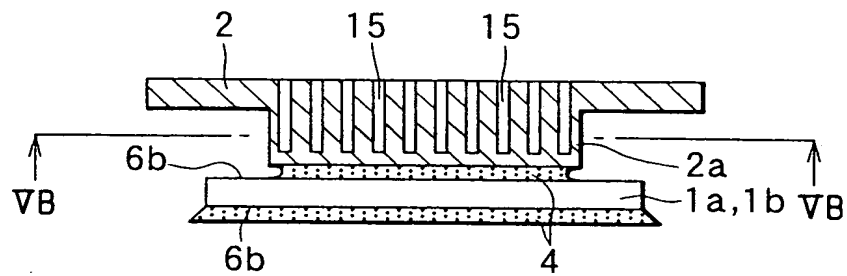


FIG. 4D

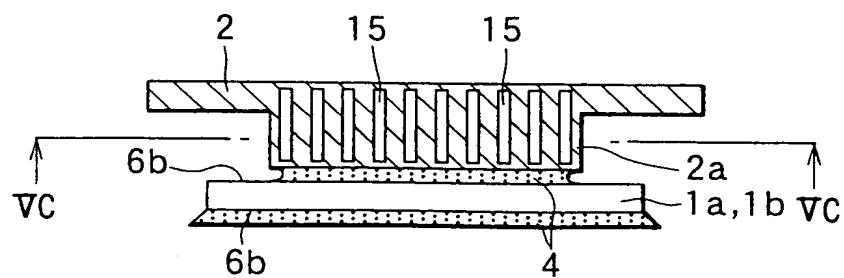


FIG. 5A

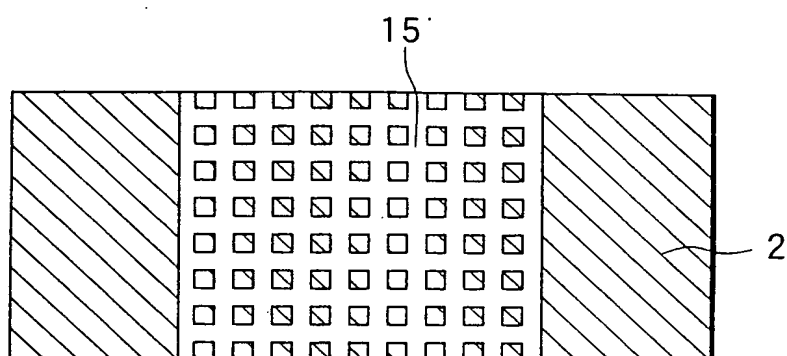


FIG. 5B

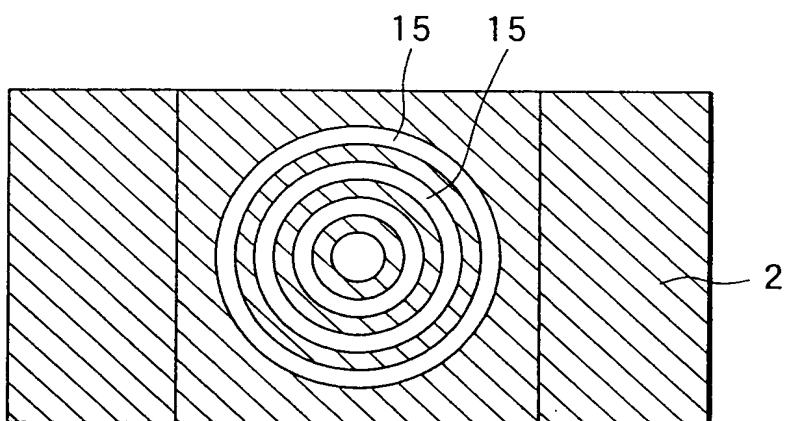
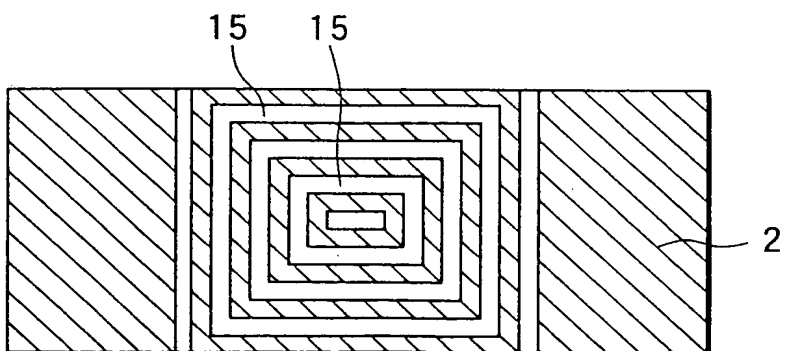


FIG. 5C



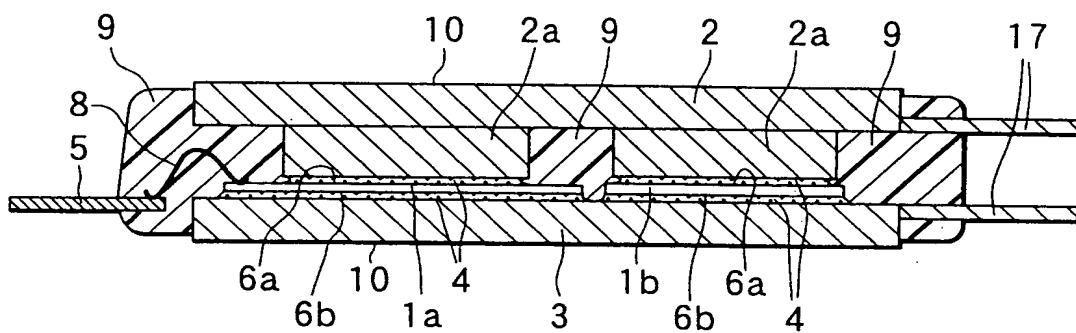


FIG. 8A

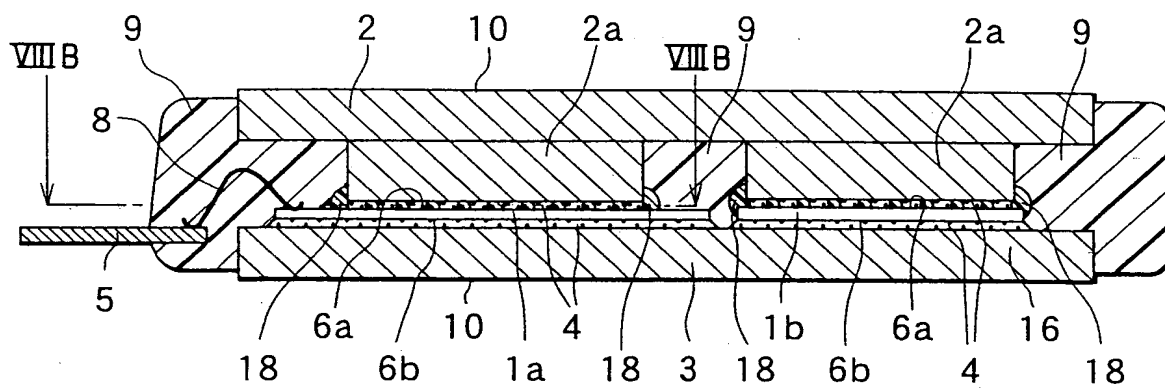


FIG. 8B

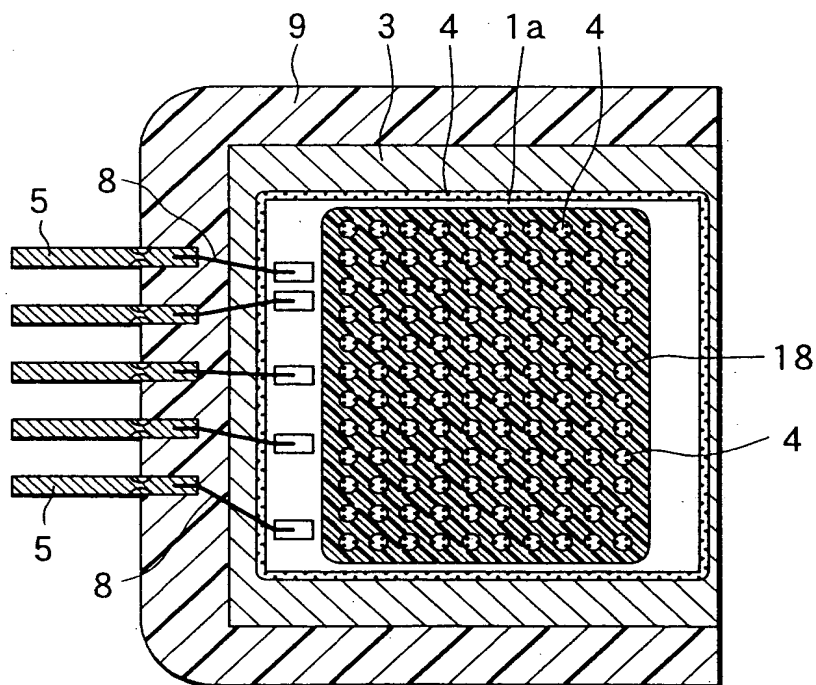


FIG. 9A

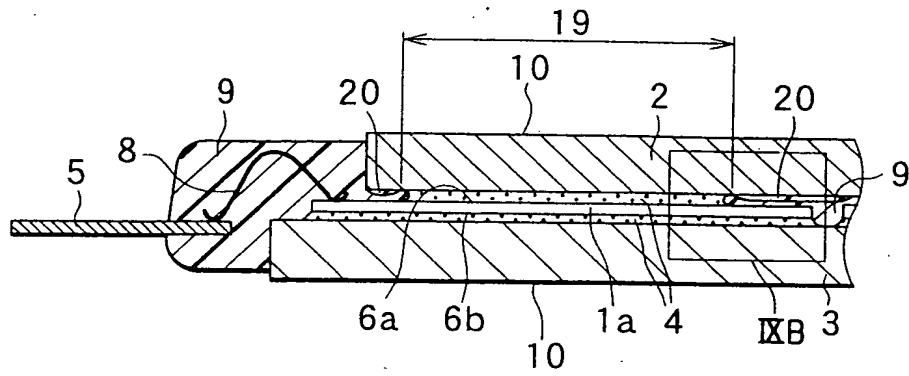


FIG. 9B

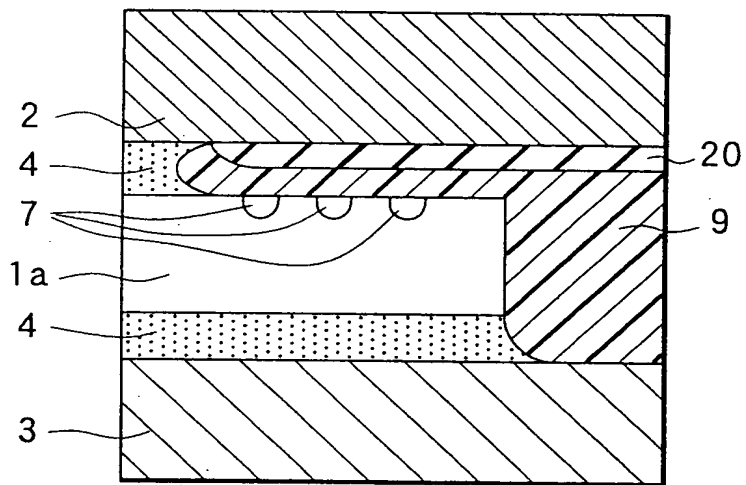


FIG. 9C

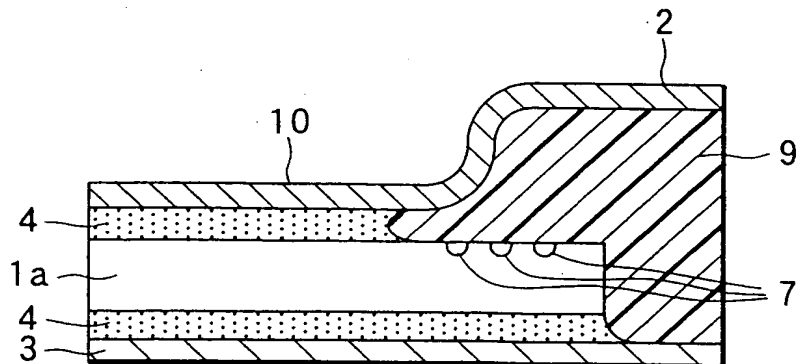


FIG. 12

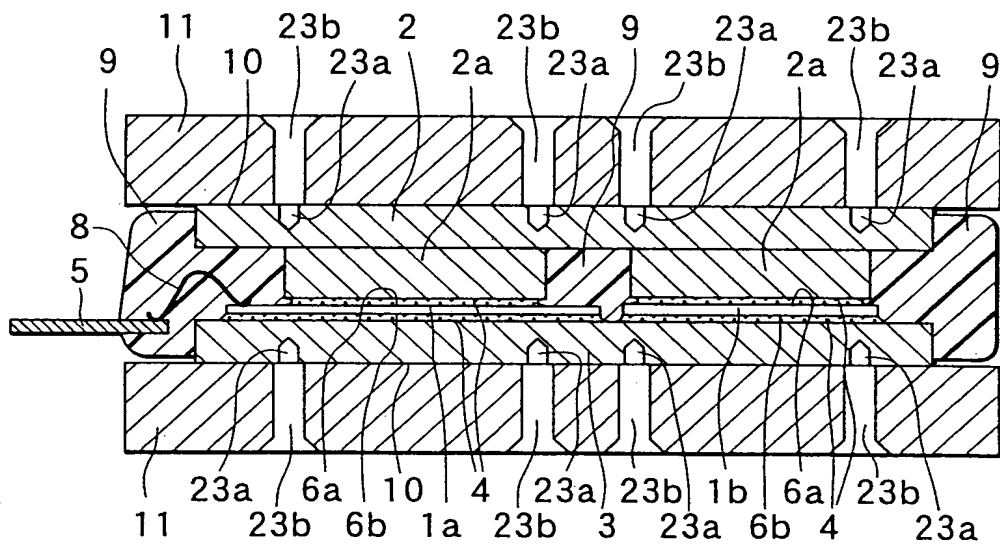
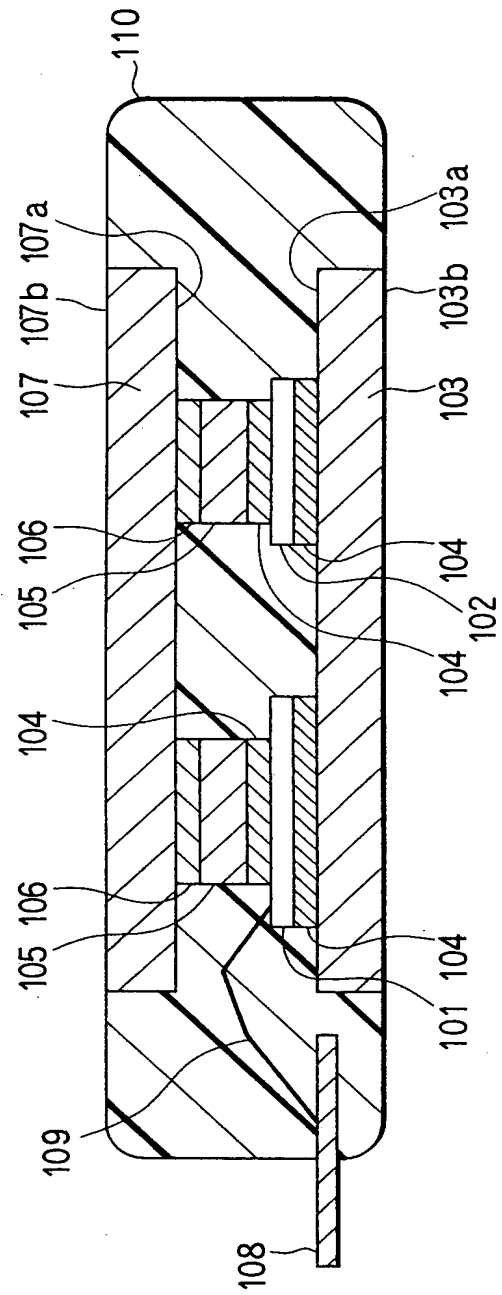


FIG. 13



A cross-sectional view of a semiconductor device 150. The device features a substrate 103 with a top layer 103a and a bottom layer 103b. Two semiconductor elements 105 are mounted on the substrate. Each element 105 consists of a semiconductor layer 104 and a top layer 101. The elements are positioned on the substrate 103, with the bottom layer 103b visible beneath them. The top layer 101 is shown as a hatched pattern, and the semiconductor layer 104 is shown as a solid pattern.

Figure 1 is a cross-sectional view of a semiconductor device. A substrate 107 is shown with a trench 107a. A layer 107c is formed on the substrate 107. A structure 101, 102 is formed on the substrate 107, and a layer 106 is formed on top of the structure 101, 102.

FIG. 16

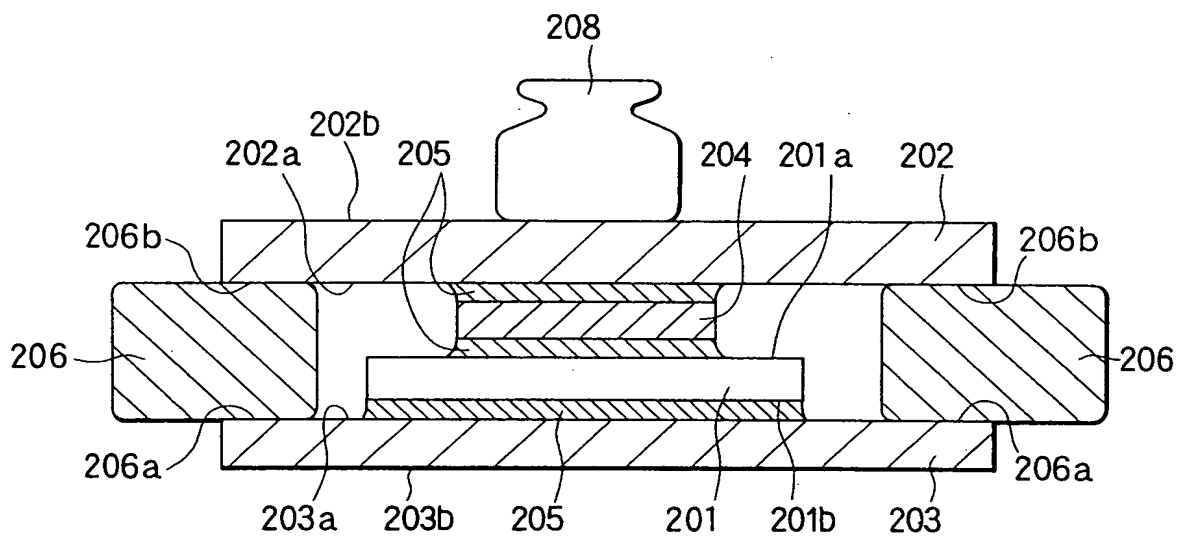
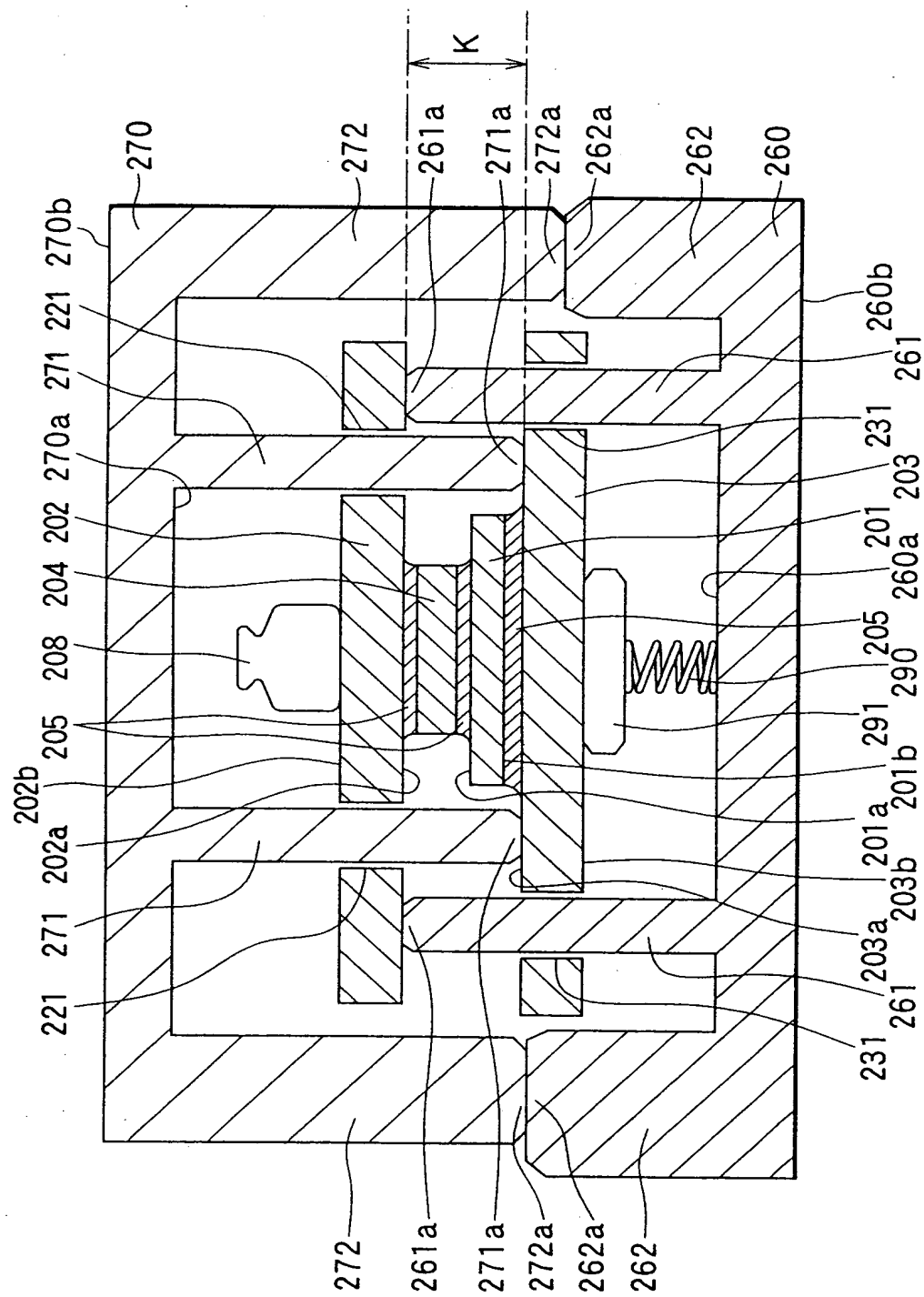


FIG. 17



816 F

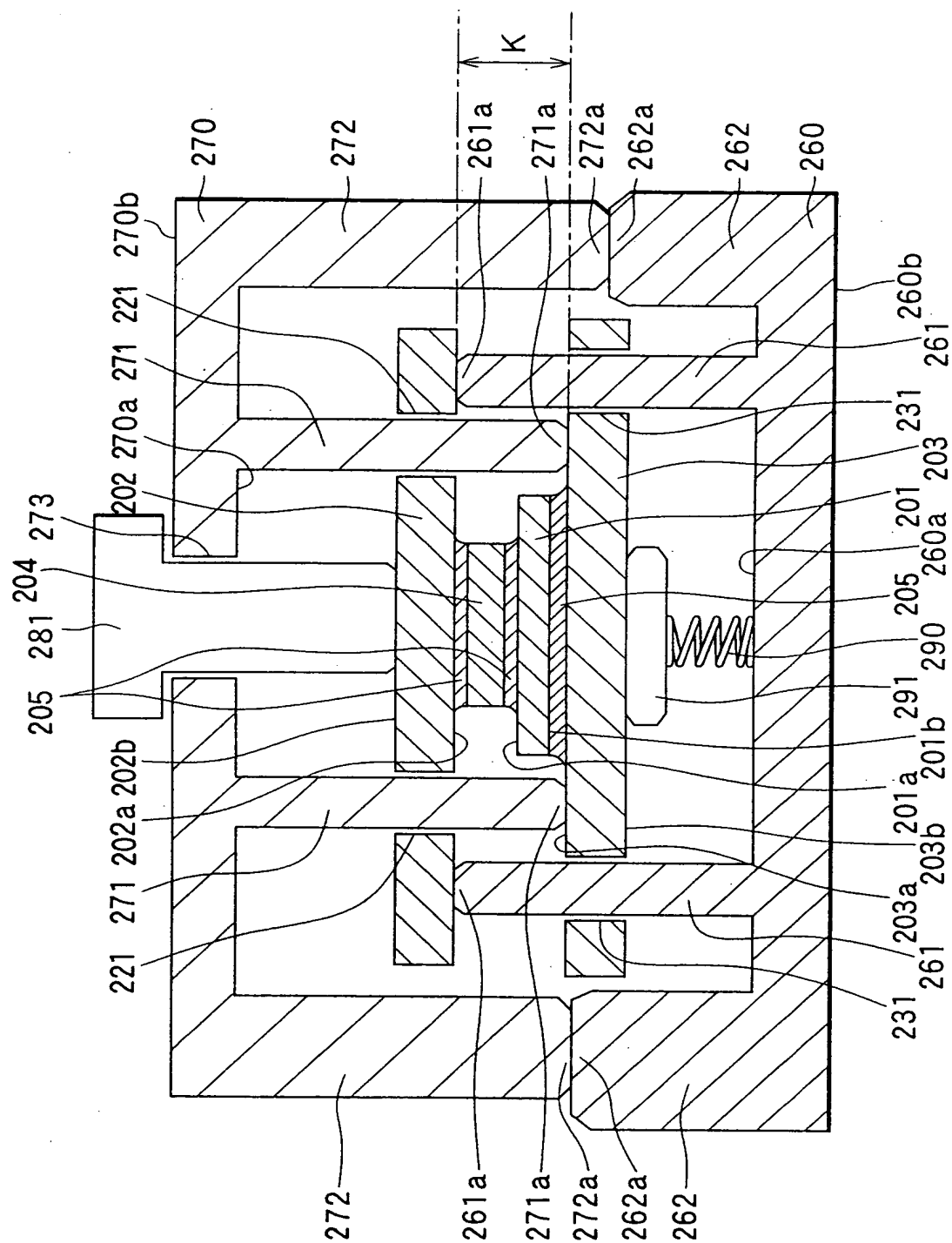


FIG. 20A

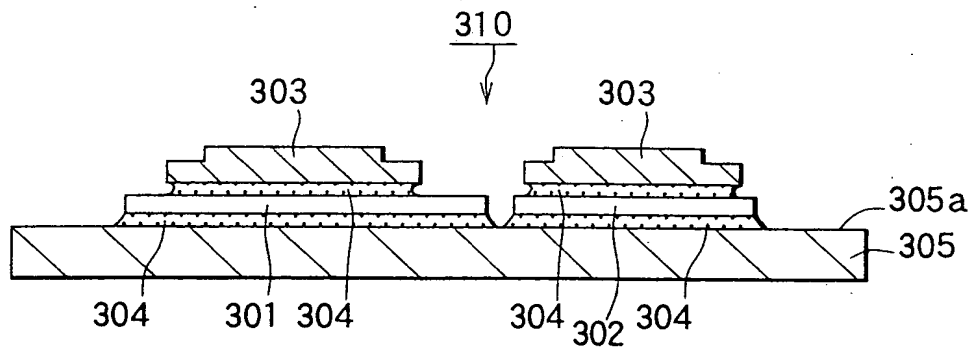


FIG. 20B

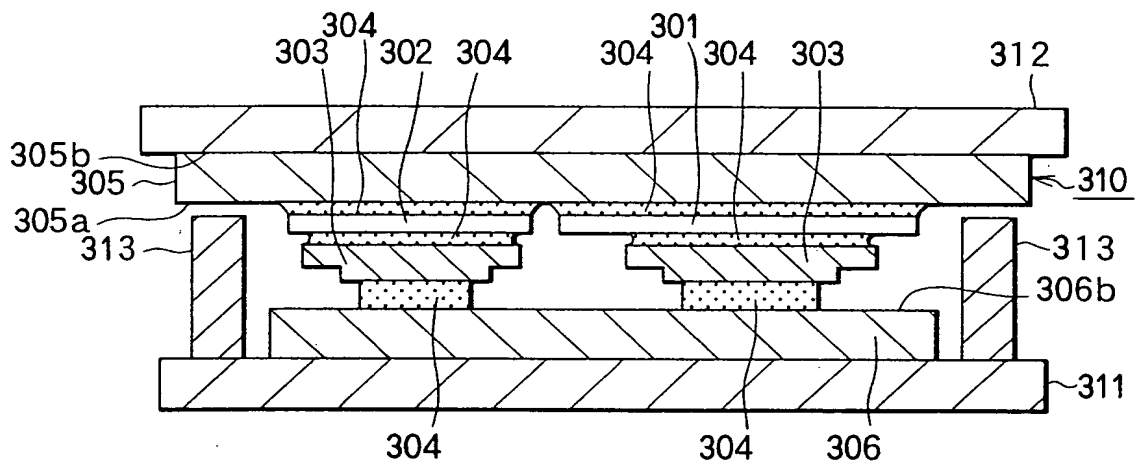


FIG. 20C

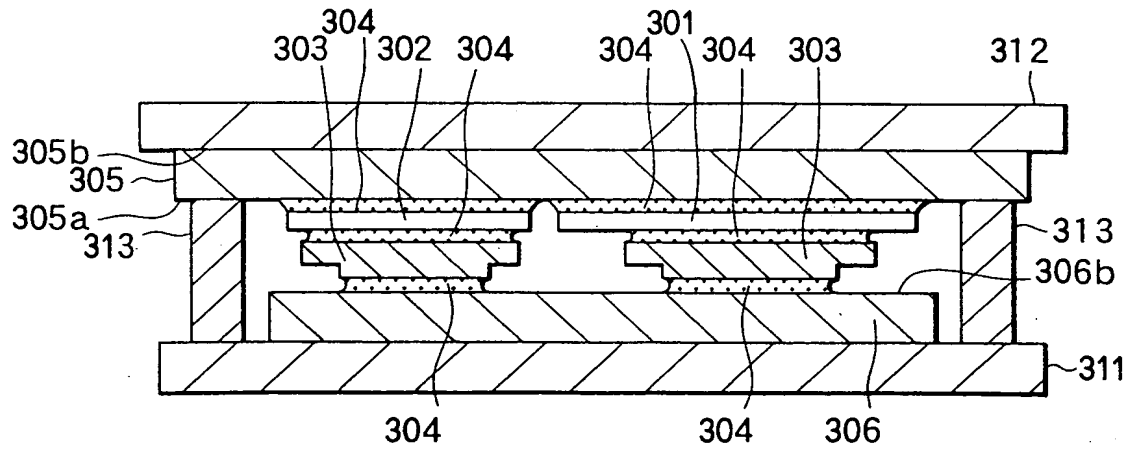


FIG. 21

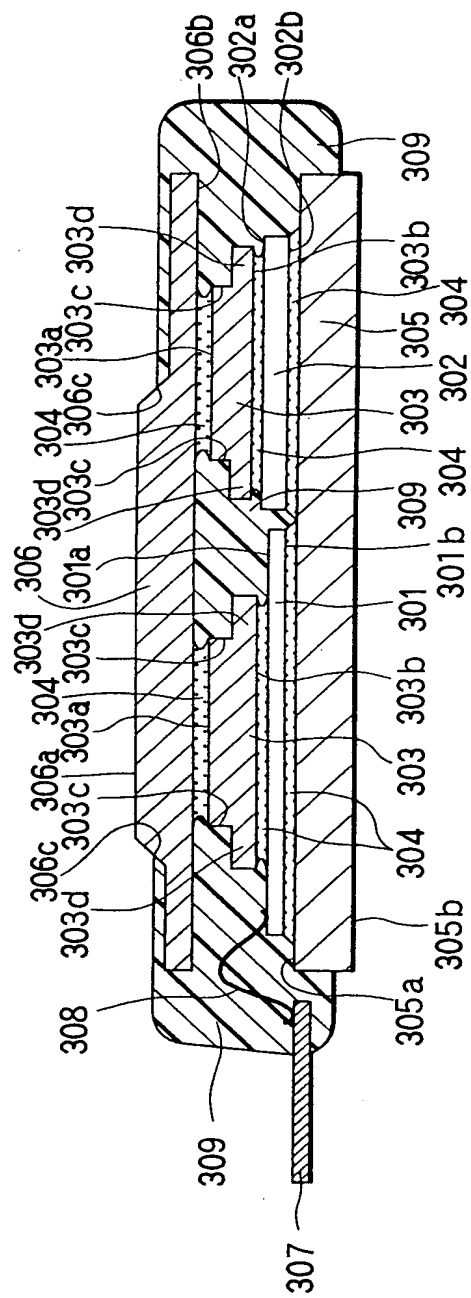
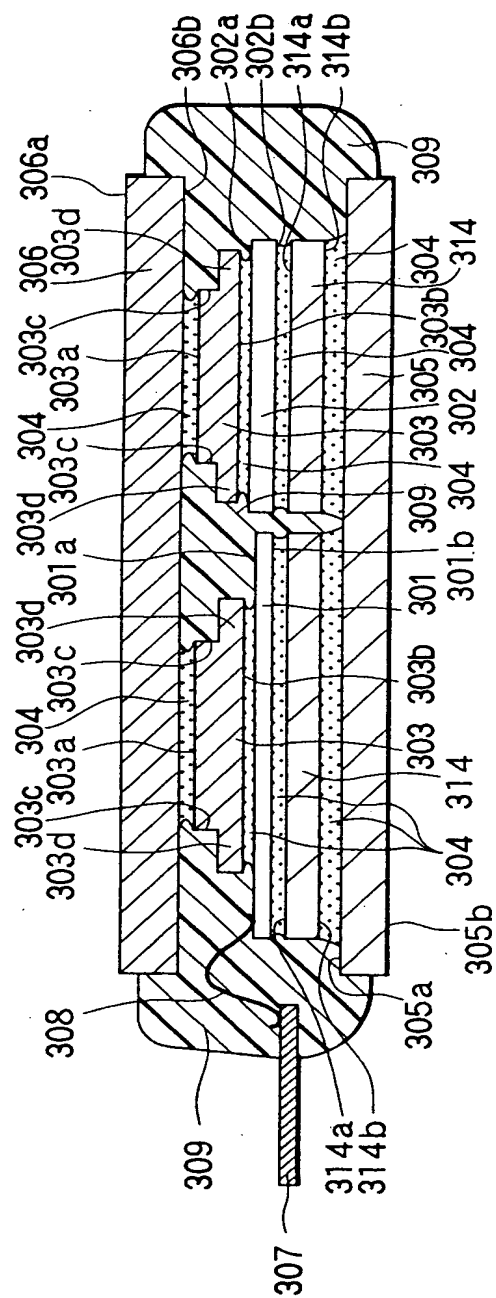


FIG. 22



[illegible]

XXVI

461 423b 423 420 422 432 431 XXV 411 408 404 400 407 421 432 401a 401b 433 435 409 453 451 433 424 434 412 431 406a 423a 405 405a 405b 452 454 455

This cross-sectional view shows a substrate 451 at the bottom. Above it is a stack of layers: 421 (topmost), 431, 112, 111, 115, and 116 (bottommost of the stack). A central block 100 is positioned within the stack, surrounded by a layer 401b. To the right of the main stack, a small structure 114 is shown, which includes layers 113, 111, and 401a.

FIG. 27

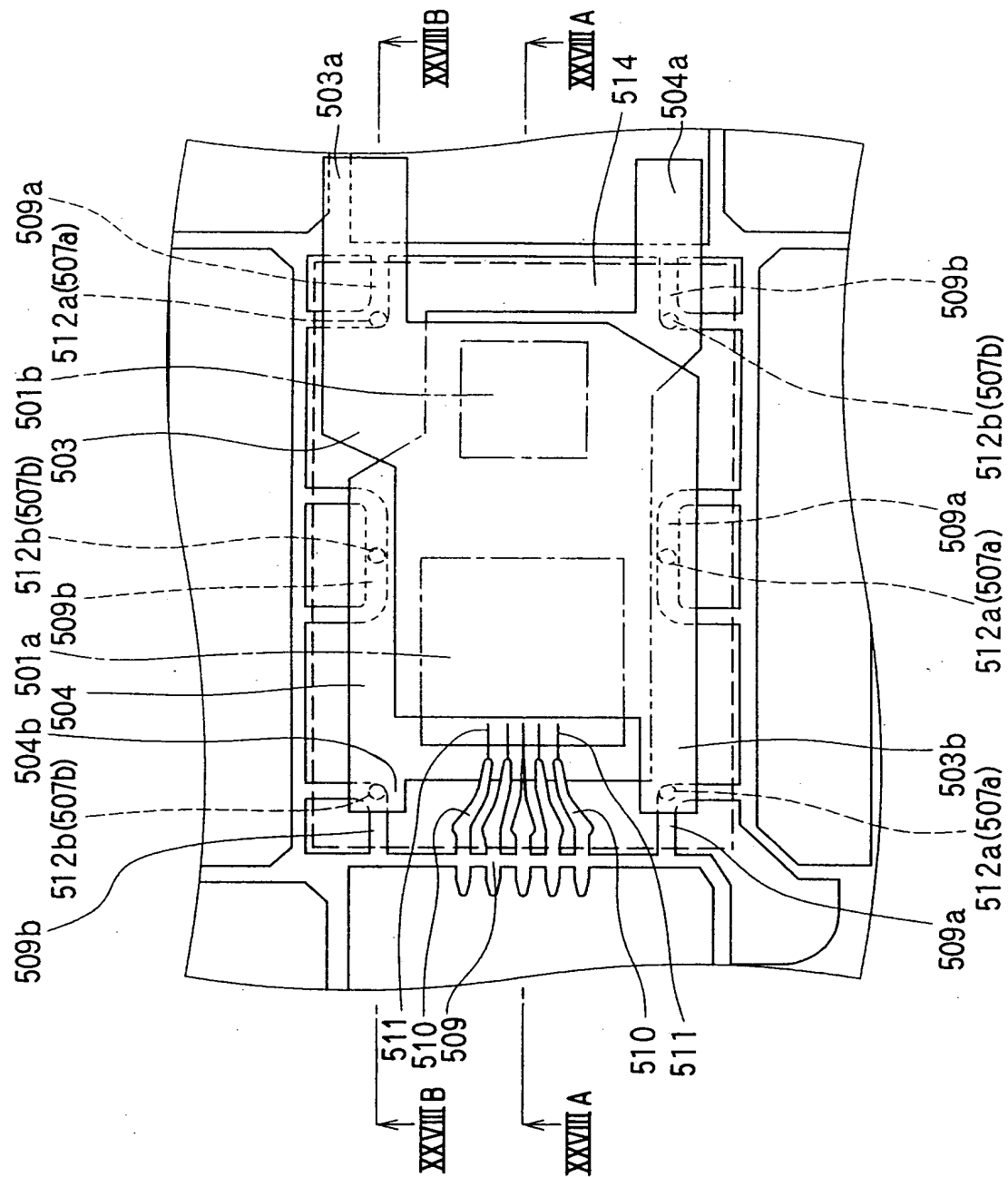


FIG. 28A

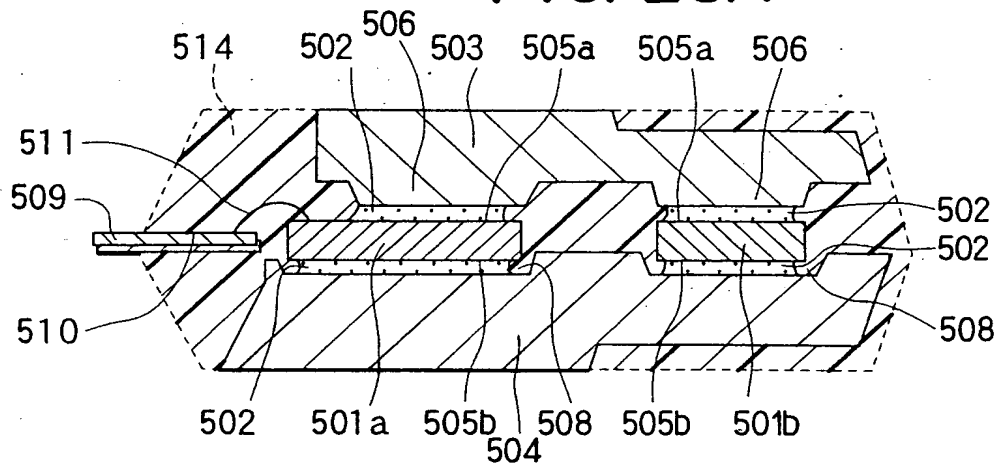


FIG. 28B

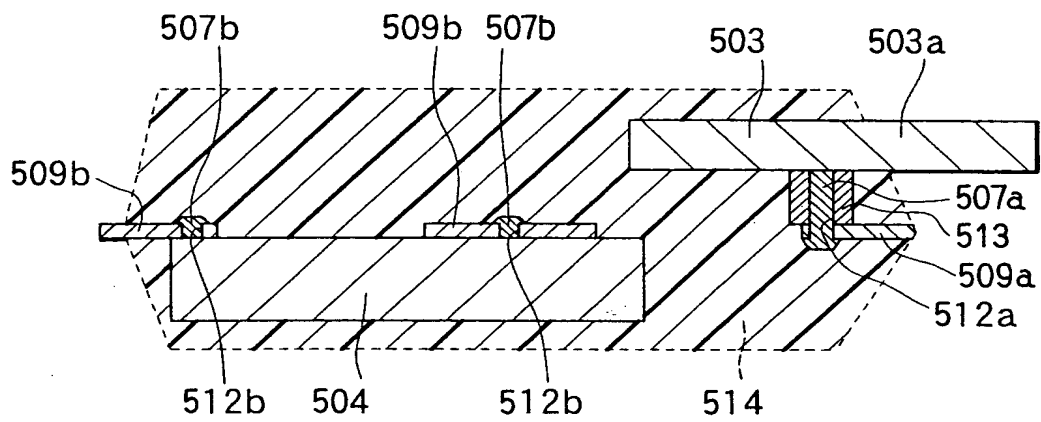


FIG. 29

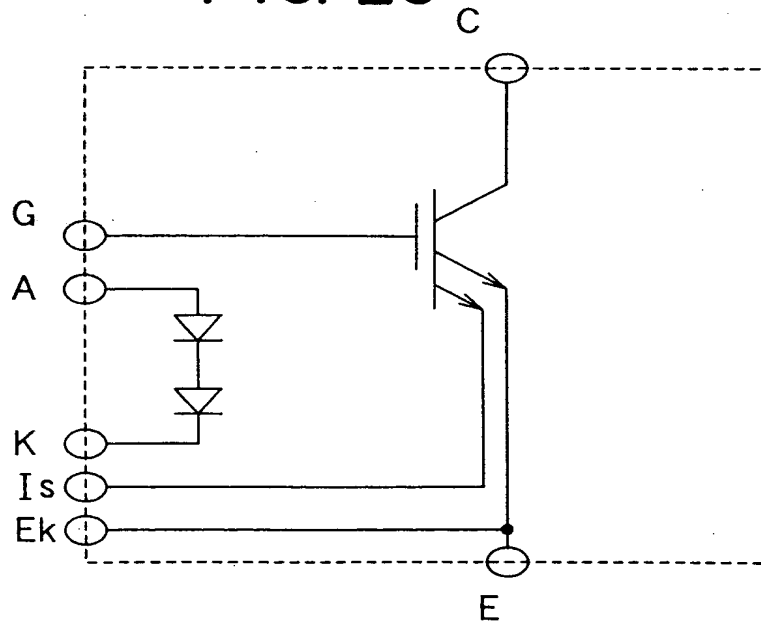


FIG. 30A

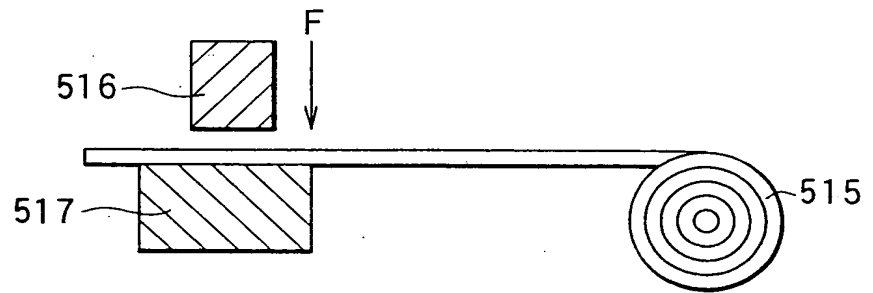


FIG. 30B

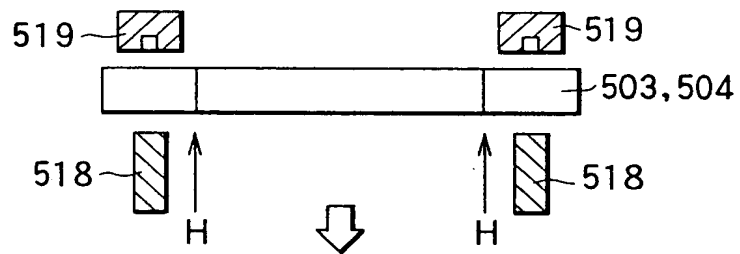


FIG. 30C

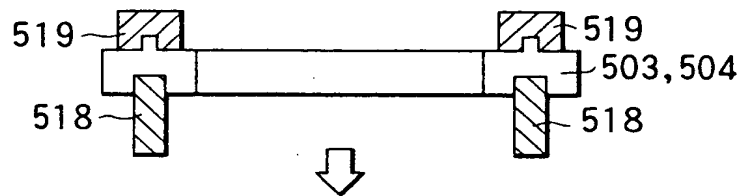


FIG. 30D



FIG. 31

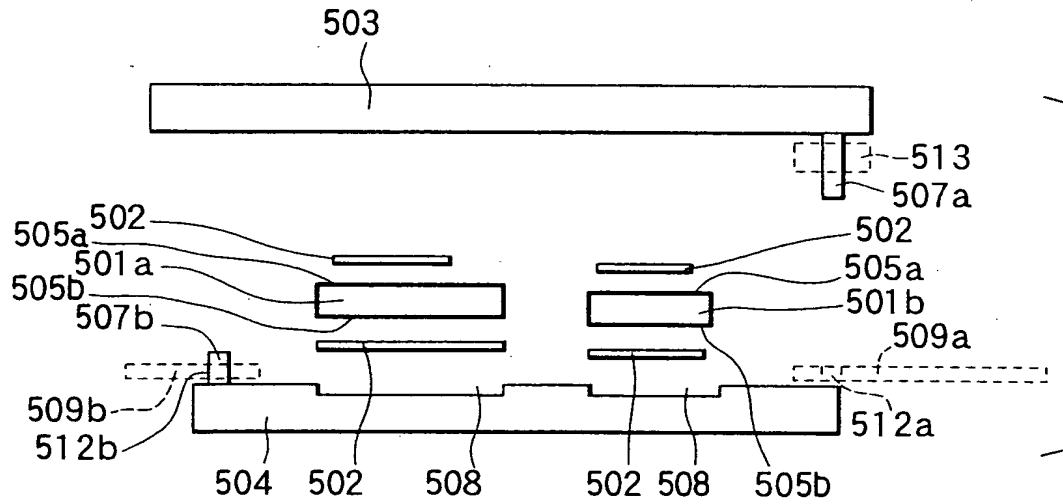


FIG. 32A

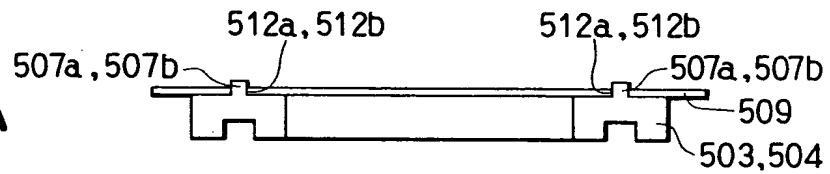


FIG. 32B

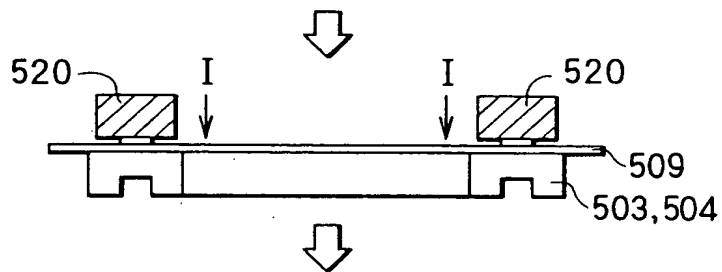


FIG. 32C

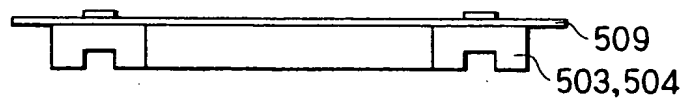


FIG. 33

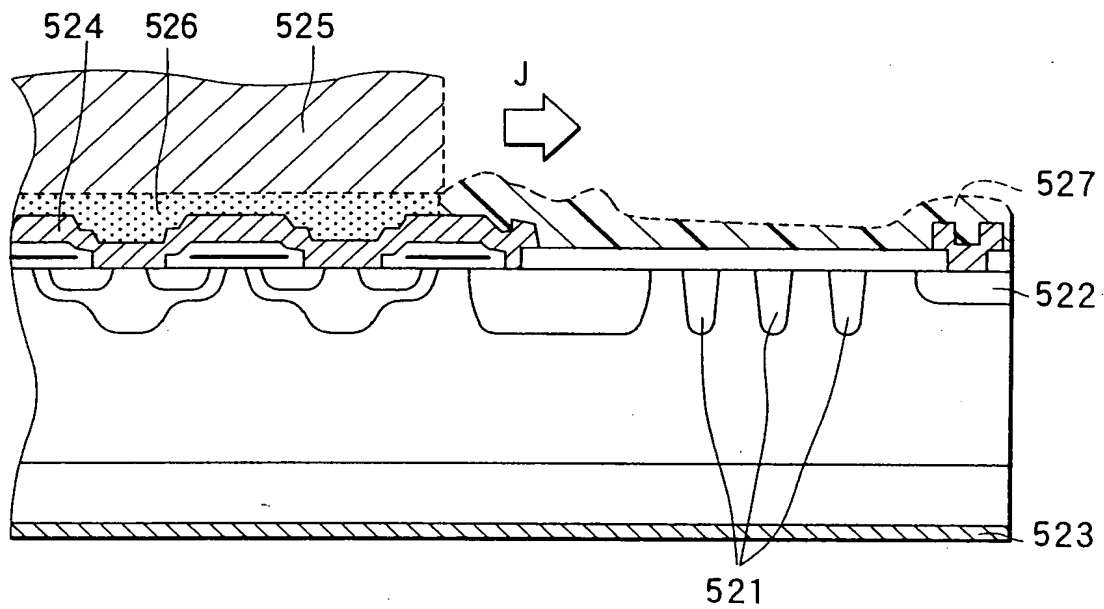


FIG. 34

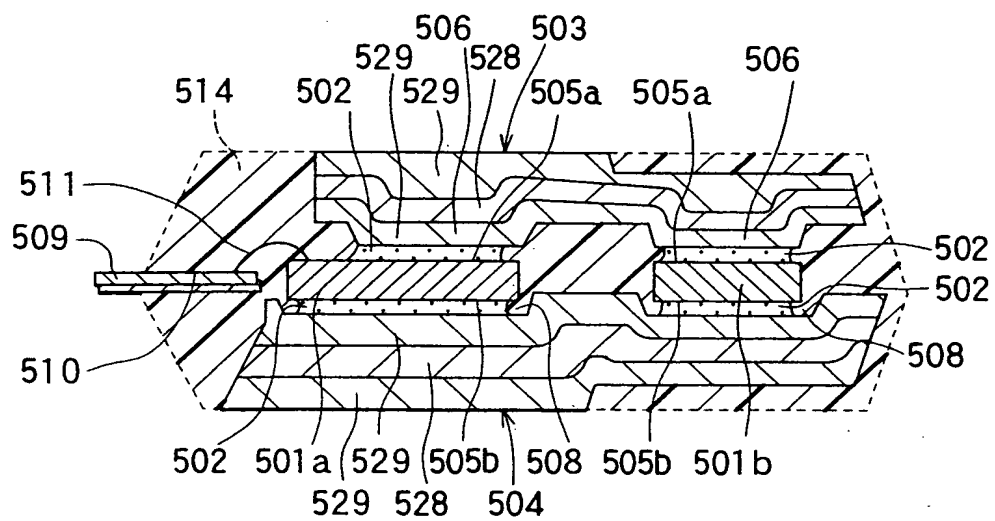


FIG. 35A

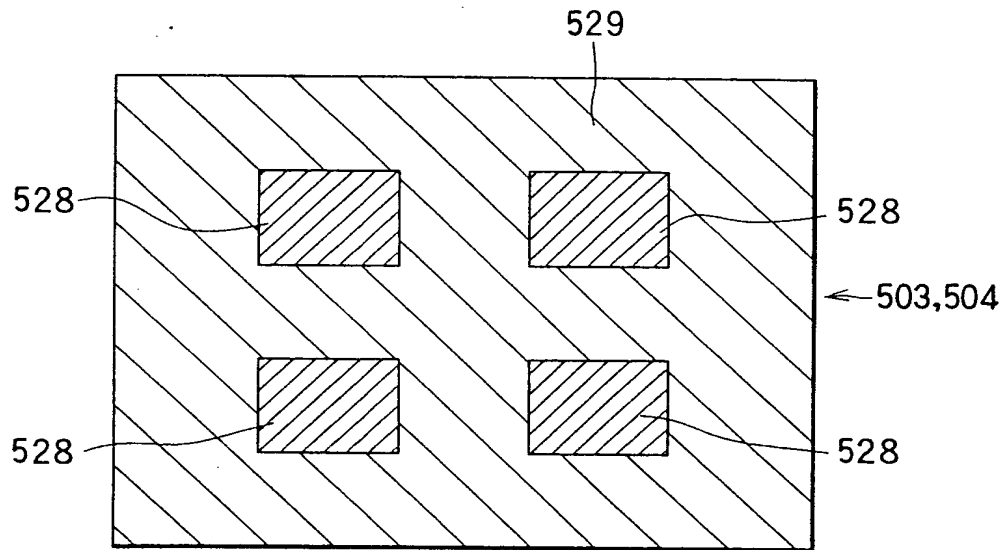


FIG. 35B

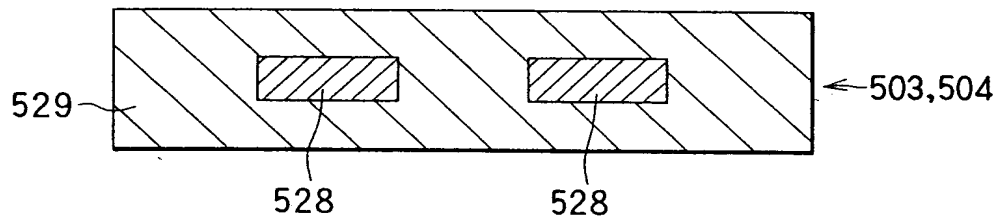


FIG. 36

